DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate MOSFETS

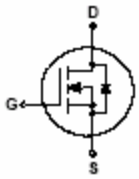
2N7002 MOSFET (N-Channel)

SOT-23

1. GATE
2. SOURCE
3. DRAIN

FEATURES

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability



Marking: 7002

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	0.115	A
Power Dissipation	P_D	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-50 ~+150	

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 μA	60			V
Gate-Threshold Voltage	$V_{th(GS)}$	V_{DS}=V_{GS}, I_D=250 μA	1		`	
Gate-body Leakage	I_{GSS}	V_{DS}=0 V, V_{GS}=±25 V			±80	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60 V, V_{GS}=0 V			80	nA
On-state Drain Current	$I_{D(ON)}$	V_{GS}=10 V, V_{DS}=7 V	500			mA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=500mA			7	Ω
		V_{GS}=5 V, I_D=50mA			7	
Forward Trans conductance	g_{fs}	V_{DS}=10 V, I_D=200mA	80			ms
Drain-source on-voltage	$V_{DS(on)}$	V_{GS}=10V, I_D=500mA	0.5		3.75	V
		V_{GS}=5V, I_D=50mA	0.05		0.375	V
Diode Forward Voltage	V_{SD}	I_S=115mA, V_{GS}=0 V	0.55		1.2	V
Input Capacitance *	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1MHz			50	pF
Output Capacitance *	C_{oss}				25	
Reverse Transfer Capacitance *	C_{rss}				5	

SWITCHING TIME

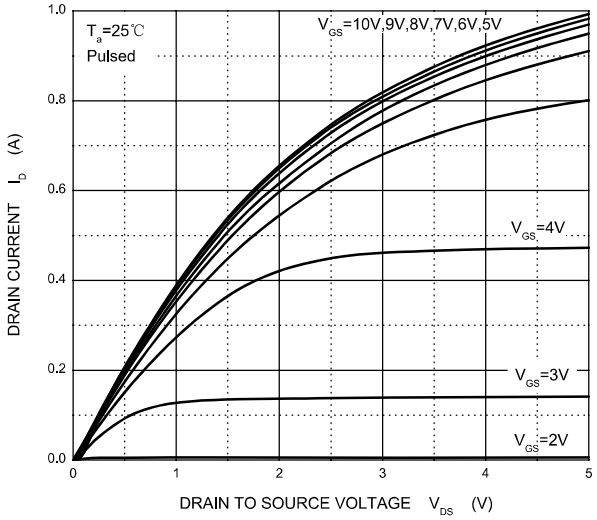
Turn-on Time *	$t_{d(on)}$	V_{DD}=25 V, R_L=50Ω, I_D=500mA, V_{GEN}=10 V R_G=25Ω			20	ns
Turn-off Time *	$t_{d(off)}$				40	

*These parameters have no way to verify.

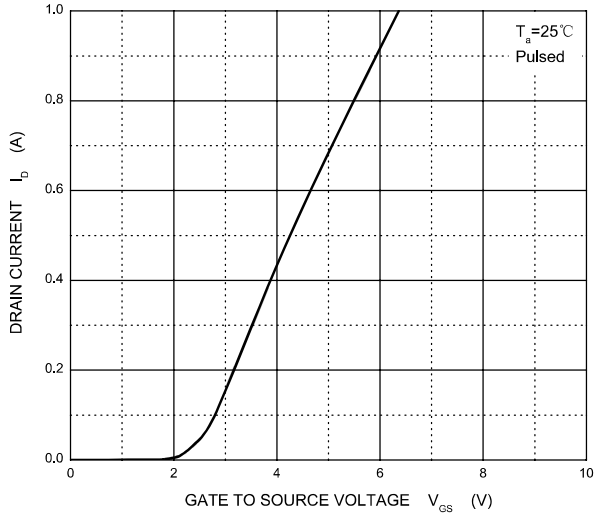
D,Apr,2012

Typical Characteristics 2N7002

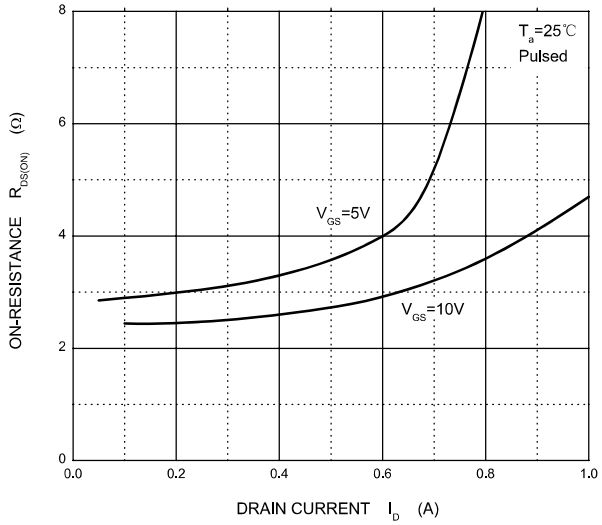
Output Characteristics



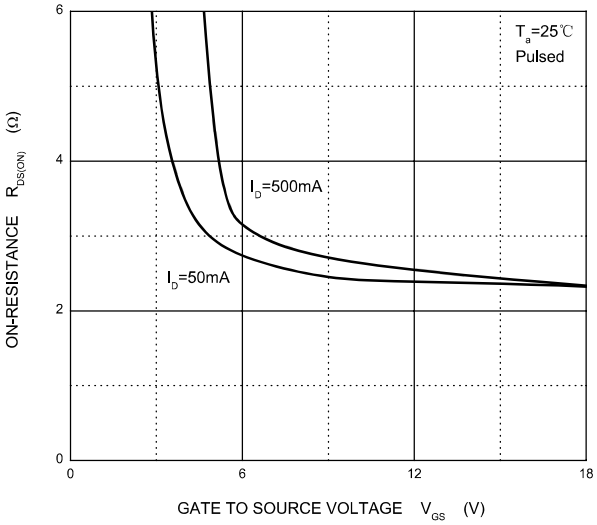
Transfer Characteristics



$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}